

ABSTRACT OF THE DISCLOSURE

A semiconductor laser includes a semiconductor layer group composed of an n-type emitter layer, a p-type base layer, an active layer, an n-type base layer and a p-type emitter layer which are successively formed on a given substrate. Then, the semiconductor layer group includes three pn junctions. The first pn junction is formed of the n-type emitter layer and the p-type base layer, and the second pn junction is formed of the p-type base layer and the n-type base layer, and the third pn junction is formed of the n-type base layer and the p-type emitter layer.